

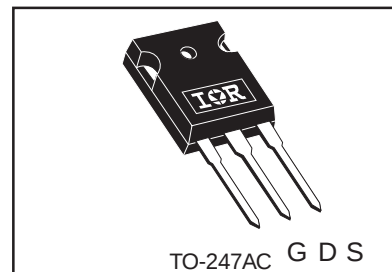
Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptable Power Supply
- High speed power switching

V_{DSS}	$R_{ds(on)}$ max	I_D
500V	0.27 Ω	20A

Benefits

- Low Gate Charge Q_g results in Simple Drive Requirement
- Improved Gate, Avalanche and dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective C_{oss} specified (See AN1001)



Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	20	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	13	
I_{DM}	Pulsed Drain Current ①	80	
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	280	W
	Linear Derating Factor	2.2	W/ $^\circ\text{C}$
V_{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	3.8	V/ns
T_J	Operating Junction and	-55 to + 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Typical SMPS Topologies:

- Full Bridge
- PFC Boost

Notes ① through ⑤ are on page 8
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IRFP460A

International
IR Rectifier

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.61	—	$V/^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.27	Ω	$V_{GS} = 10V, I_D = 12A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	25 250	μA	$V_{DS} = 500V, V_{GS} = 0V$ $V_{DS} = 400V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	11	—	—	S	$V_{DS} = 50V, I_D = 12A$
Q_g	Total Gate Charge	—	—	105	nC	$I_D = 20A$
Q_{gs}	Gate-to-Source Charge	—	—	26		$V_{DS} = 400V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	42	ns	$V_{GS} = 10V$, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	18	—		$V_{DD} = 250V$
t_r	Rise Time	—	55	—		$I_D = 20A$
$t_{d(off)}$	Turn-Off Delay Time	—	45	—		$R_G = 4.3\Omega$
t_f	Fall Time	—	39	—		$R_D = 13\Omega$, See Fig. 10 ④
C_{iss}	Input Capacitance	—	3100	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	480	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	18	—		$f = 1.0MHz$, See Fig. 5
C_{oss}	Output Capacitance	—	4430	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$
C_{oss}	Output Capacitance	—	130	—		$V_{GS} = 0V, V_{DS} = 400V, f = 1.0MHz$
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	140	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 400V$ ⑤

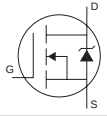
Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	960	mJ
I_{AR}	Avalanche Current①	—	20	A
E_{AR}	Repetitive Avalanche Energy①	—	28	mJ

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.45	$^\circ\text{C/W}$
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient	—	40	

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	20	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	80		
V_{SD}	Diode Forward Voltage	—	—	1.8	V	$T_J = 25^\circ\text{C}, I_S = 20A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	480	710	ns	$T_J = 25^\circ\text{C}, I_F = 20A$
Q_{rr}	Reverse Recovery Charge	—	5.0	7.5	μC	$di/dt = 100A/\mu\text{s}$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

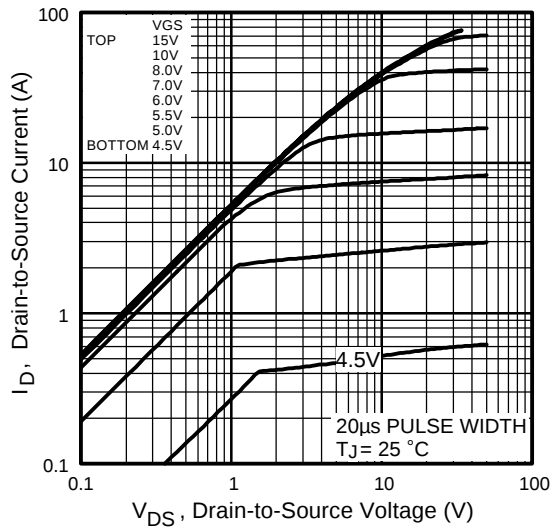


Fig 1. Typical Output Characteristics

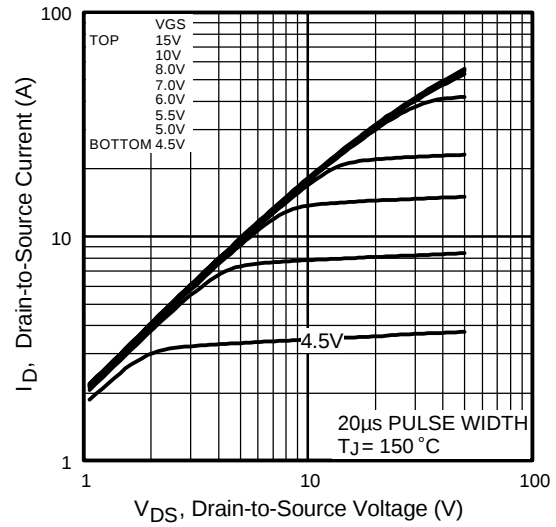


Fig 2. Typical Output Characteristics

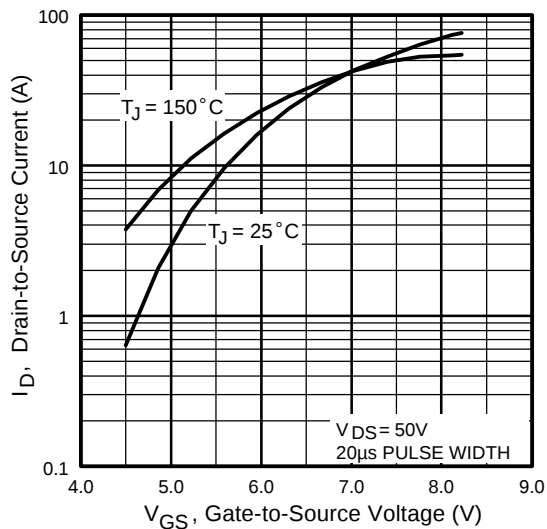


Fig 3. Typical Transfer Characteristics

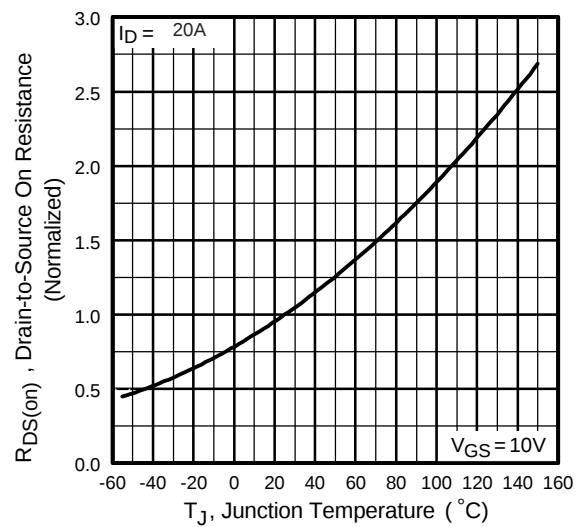


Fig 4. Normalized On-Resistance Vs. Temperature

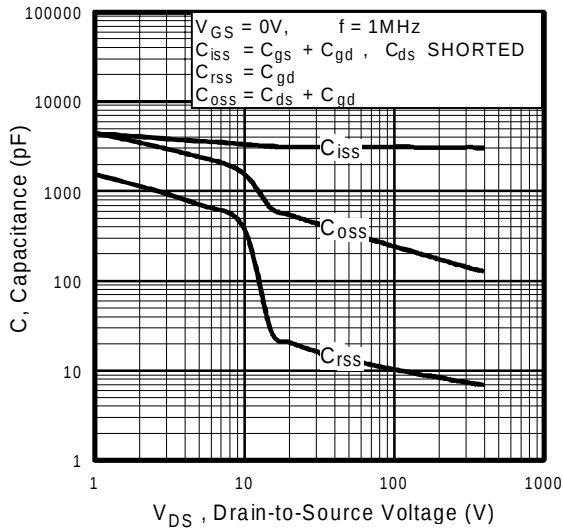


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

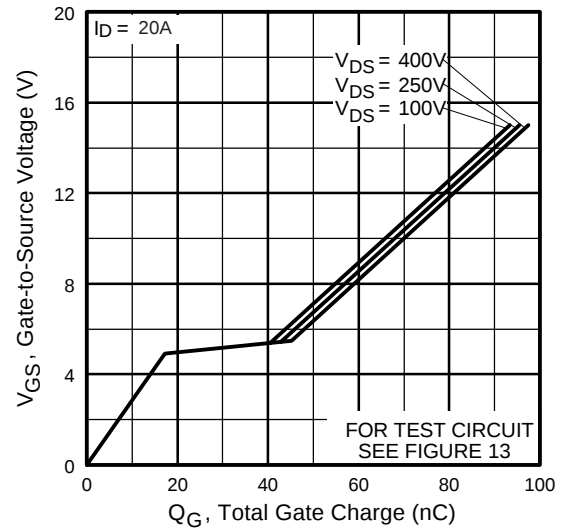


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

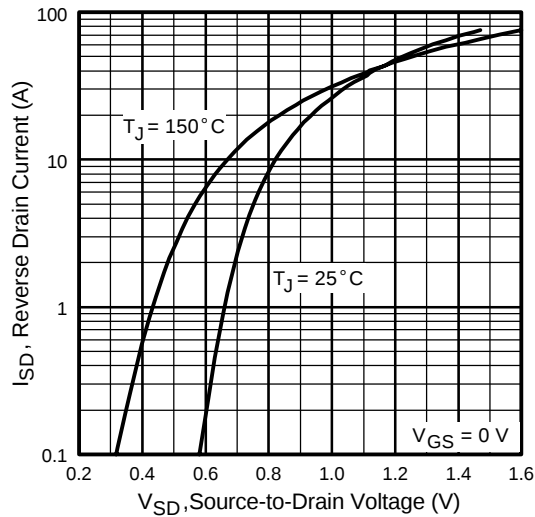


Fig 7. Typical Source-Drain Diode Forward Voltage

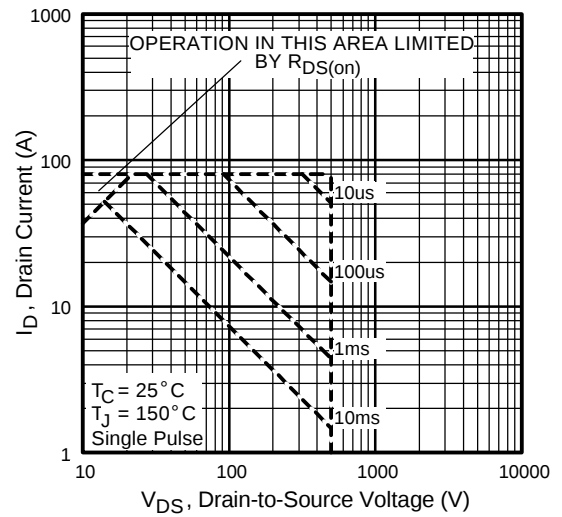


Fig 8. Maximum Safe Operating Area

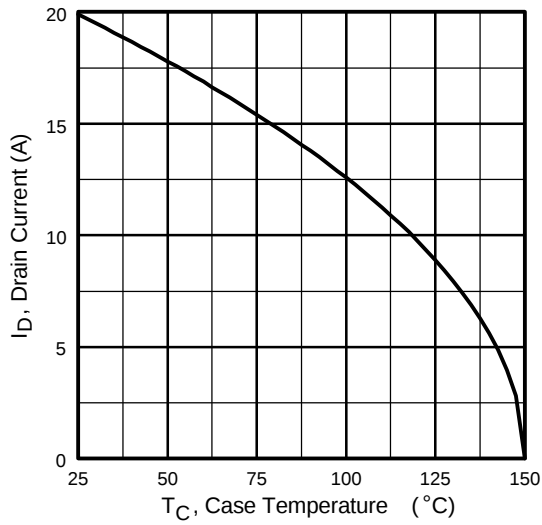


Fig 9. Maximum Drain Current Vs. Case Temperature

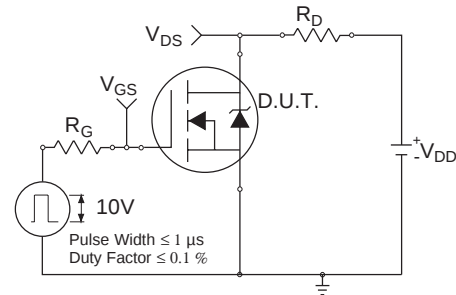


Fig 10a. Switching Time Test Circuit

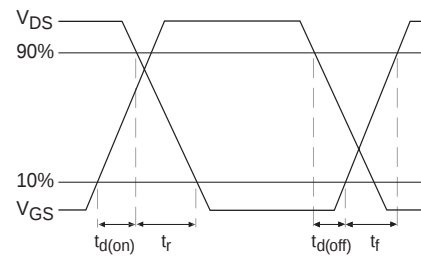


Fig 10b. Switching Time Waveforms

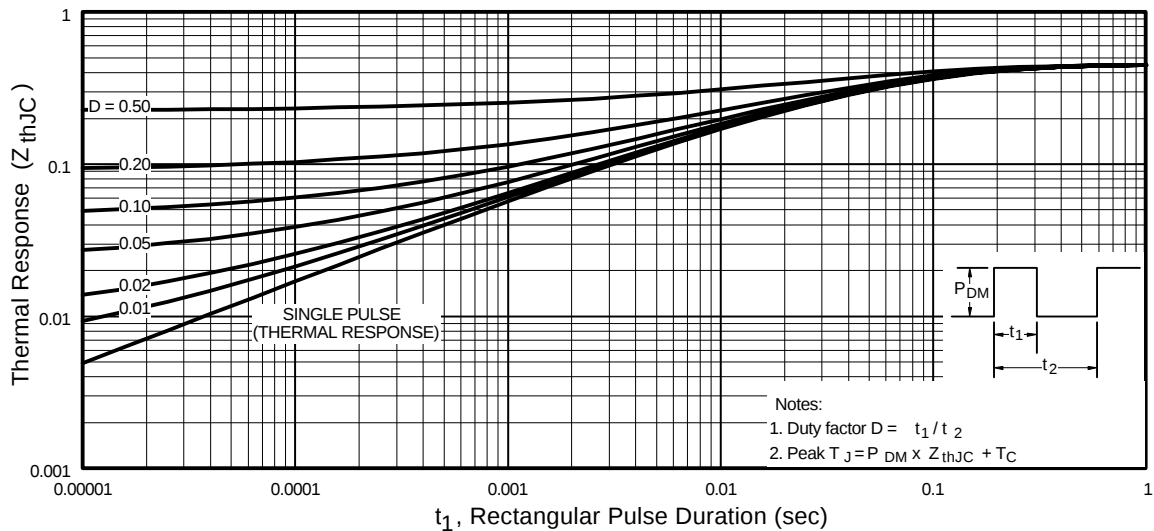


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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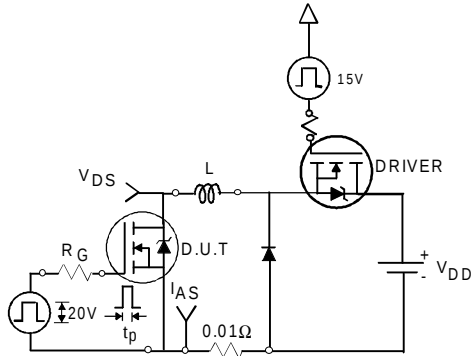


Fig 12a. Unclamped Inductive Test Circuit

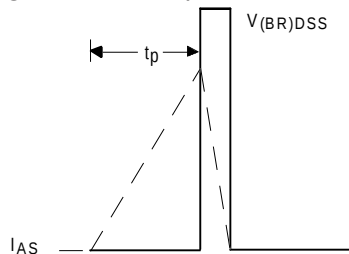


Fig 12b. Unclamped Inductive Waveforms

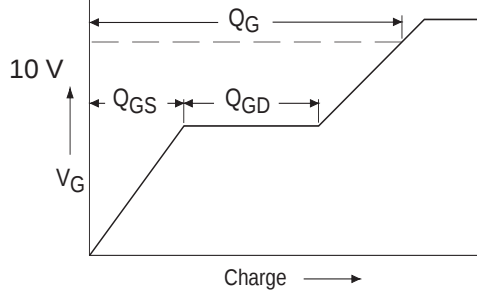


Fig 13a. Basic Gate Charge Test Circuit

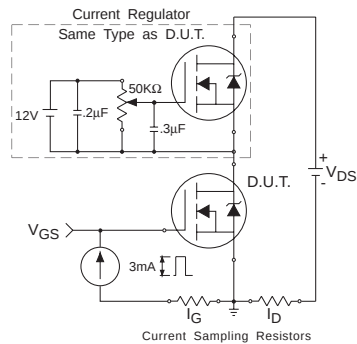


Fig 13b. Gate Charge Test Circuit

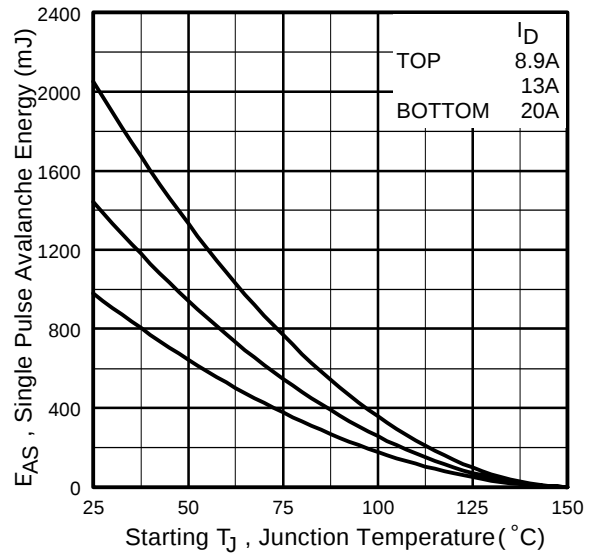


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

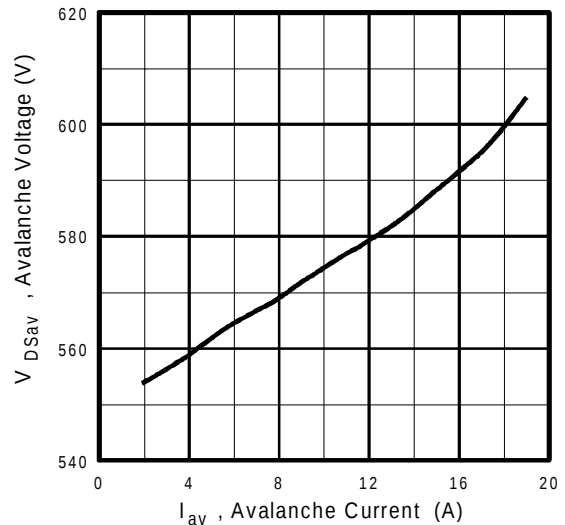
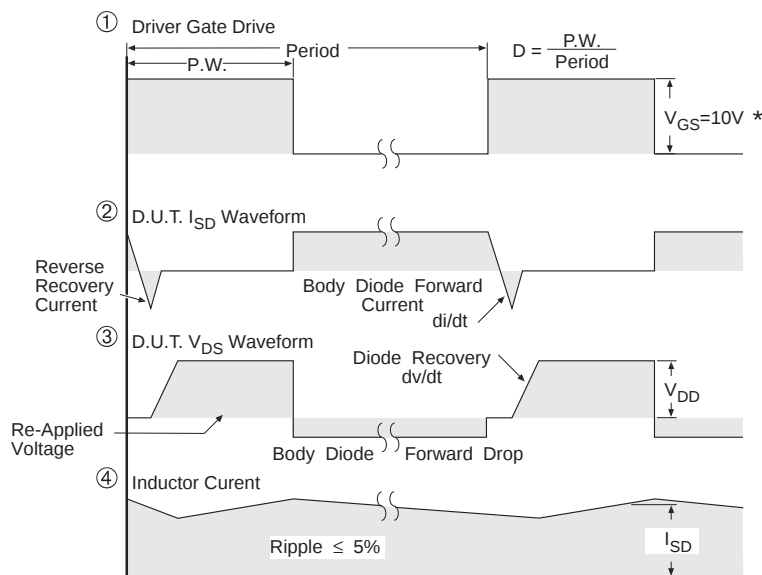
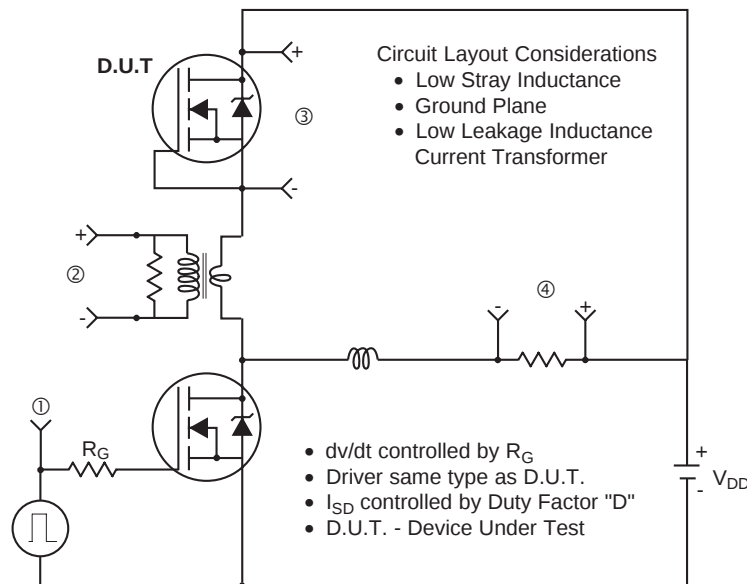


Fig 12d. Typical Drain-to-Source Voltage Vs. Avalanche Current

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Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFETS

Dimensions are shown in millimeters (inches)

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